

²
~~14~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,

wherein said ceramic substrate is used in a temperature range of 100°C to 700°C.

³
~~15~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,

wherein said ceramic substrate has a plurality of through holes in which lifter pins are inserted.

⁴
~~16~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,

wherein said conductor is formed in a region up to the position of 60% in a thickness-direction from a face opposite to a wafer treating face of ceramic substrate.

⁵
~~17~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,

wherein said ceramic substrate contains 0.05 to 10% by weight of oxygen.

⁶
~~18~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,

wherein said ceramic substrate contains an oxide as a sintering aid.

⁷
~~19~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,

wherein said ceramic substrate contains a sintering aid comprising at least one member selected from the group consisting of an alkali metal oxide, an alkaline earth metal oxide and a rare-earth oxide.

⁸
~~20~~. (New) The ceramic heater for a semiconductor-producing/examining device according to Claim ~~13~~,